PERSONAL INFORMATION

Gaudenzio Meneghesso

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Sex: Ma e | *Nationality* Ita an

Enterprise	University	EPR
☐ Management Level	☒ Full professor	☐ Research Director and 1st level Technologist / First Researcher and 2nd level Technologist
☐ Mid-Management Level	☐ Associate Professor	☐ Level Researcher and Technologist
☐ Employee / worker level	☐ Researcher and Technologist of V V V and V level / Technical collaborator	☐ Researcher and Technologist of V V V and V level / Technical collaborator

WORK EXPERIENCE

2018-today

Department's Director

Un vers ty of Padova – Department of Informat on Eng neer ng (www.de .un pd. t)
Bus ness or sector **Information Communication Technologies - ICT**

2011-today

Full Professor

Un vers ty of Padova – Department of Informat on Eng neer ng (www.de .un pd. t)
- Bus ness or sector **Microelectronics Engineering**
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2022-2011

Associate Professor

Un vers ty of Padova – Department of Informat on Eng neer ng (www.de .un pd. t)
Bus ness or sector **Microelectronics Engineering**

1998-2002

Researcher

Un vers ty of Padova – Department of Inofrmat on Eng neer ng (www.de .un pd. t)
Bus ness or sector **Microelectronics Engineering**

EDUCATION AND TRAINING

1994-1997

Ph.D. Electrical and Telecommunication Engineering EQF8

Un vers ty of Padova – Department of Informat on Eng neer ng (www.de .un pd. t)
- Character zat on of dev ces on compound sem conductors (GaAs, InP,)
- Hot-e ectron character zat on, effects and re ab ty of GaAs-based and InP-based HEMT's and pseudomorph c HEMT's

1992-1994

Research assistance for international project EQF7

Un vers ty of Padova – Department of Informat on Eng neer ng (www.de .un pd. t)
- Character zat on of dev ces on compound sem conductors (GaAs, InP,)
- Hot-e ectron character zat on, effects and re ab ty of GaAs-based and InP-based HEMT's

1986-1992

Laurea Degree in Electronic Engineering

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- Hot-e ectron character zat on, effects and re ab ty of GaAs-based and InP-based HEMT's

Expertise.

His research interests are:

a) Power devices on wide bandgap semiconductors (GaN, SiC)
b) Microwave and optoelectronics devices on III-V and III-N;
c) RF-MEMS switches for reconfigurable antenna arrays;
d) Electrostatic discharge (ESD) protection structures;
e) organic semiconductors devices;
f) photovoltaic solar cells.

Within these activities, he published **more than 800 technical papers** (of which more than 100 Invited Papers and 14 best paper awards).
Bibliometric indexes (**updated January 2022**):

- **Scopus:** Documents: **692**, Tot. Citations **11671**, h-index: **51**
- **Google Scholar:** Documents: **861**, Tot. Citations **15771**, h-index: **62**

He has been the local coordinator of several research project (H2020, ENIAC, ECSEL, PRIN.) and the Prime responsible of several research contract with industry and research institute. Nowadays he is the **Project Coordinator** of a European project H2020 – InRel-NPower (http://www.inrel-npower.eu/) H2020-NMBP-2016-2017, Grant Agreement number 720527.

He is reviewer of several international journals: IEEE Transactions on Electron Devices, IEEE Electron Device Letters, IEE Electronics Letters, Journal of Applied Physics, Applied Physics Letters and Semiconductor Science and Technology (IOP), Microelectronics Reliability (Elsevier).

He served several years for the IEEE-International Electron Device Meeting (IEDM): he was in the Quantum Electronics and Compound Semiconductors sub-committee as a member in 2003, and 2017 as chair in 2004 and 2005 while in 2006 and 2007 he has been in the Executive Committee as European Arrangements Chair. He is also serving the IEEE International Electron Device Meeting (IEDM) since 2017 as TPC committee member.

He is serving since 2005 in the TPC of the IEEE International Reliability Physics (IRPS) Symposium (being TPC Chair of the Compound Semiconductor from 2008 to 2010) and since 2009 he is with the management committee. He has been be the **Technical Program Committee Chair of IEEE IRPS 2018**, **the vice General Chair of IEEE IRPS 2019, and the General Chair of IEEE IRPS 2020.** He has been the General Chairs of several other conferences and Workshops.

He has been **Associate Editor of IEEE Electron Device Letters and of the IEEE Transaction on Electron Devices** for the compound semiconductor devices area.

He has been nominated to **IEEE Fellow class 2013**, with the following citation: “for contributions to the reliability physics of compound semiconductors devices”.

PERSONAL SKILLS

Mother tongue(s)	Ita an
Other Language (s)	Eng sh
Job-re ated sk s	See above
D g ta sk s	Very good n d g ta sk s (L nked n, Facebook, operat ona systems, …..)

ADDITIONAL INFORMATION

Pub cat ons **Top 5 most cited Publications related to the National Center (updated January 2022)**

1. H. Amano, Y. Ba nes, E. Beam, ….. G. Meneghesso, …., Y. Zhang, “The 2018 GaN power e ectron cs roadmap”, TOPICAL REVIEW, J. Phys. D: App . Phys. 51 (2018) 163001: “**Reliability of GaN power devices: normally-on and normally-off**”, pp.18-20, ISSN: 00223727, **doi: 10.1088/1361-6463/aaaf9d Cited 489 times.**
2. Meneghesso, G., Verze es , G., Danes n, F., Rampazzo, F., Zanon, F., Tazzo , A., Menegh n , M., Zanon , E., **Reliability of GaN high-electron-mobility transistors: State of the art and perspectives**, (2008) IEEE Transact ons on Dev ce and Mater a s Re ab ty, 8 (2), art. no. 4497830, pp. 332-343. **DOI: 10.1109/TDMR.2008.923743 Cited 489 times.**
3. Meneghesso, G., Verze es , G., P erobon, R., Rampazzo, F., Ch n , A., M shra, U.K., Cana , C., Zanon , E., **Surface-related drain current dispersion effects in AlGaN-GaN HEMTs,** (2004) IEEE Transact ons on E ectron Dev ces, 51 (10), pp. 1554-1561. **DOI: 10.1109/TED.2004.835025**, **Cited 266 times.**
4. B s , D., Menegh n , M., De Sant , C., Ch n , A., Dammann, M., Bruckner, P., M ku a, M., Meneghesso, G., Zanon , E. **Deep-level characterization in GaN HEMTs-Part I: Advantages and limitations of drain current transient measurements** (2013) IEEE Transact ons on E ectron Dev ces, 60 (10), art. no. 6605590, pp. 3166-3175. **DOI: 10.1109/TED.2013.2279021**, **Cited 242 times.**
5. Meneghesso, G., Rampazzo, F., Kordoš, P., Verze es , G., Zanon , E., **Current collapse and high-electric-field reliability of unpassivated GaN/AlGaN/GaN HEMTs**, (2006) IEEE Transact ons on E ectron Dev ces, 53 (12), pp. 2932-2940. **DOI: 10.1109/TED.2006.885681**, **Cited 137 times**.